

# Silicon NPN Power Transistor

# DESCRIPTION

- Excellent Safe Operating Area
- DC Current Gain-h<sub>FE</sub>=20-70@I<sub>C</sub> = 4A
- Collector-Emitter Saturation Voltage-: V<sub>CE(sat</sub>)= 1.1 V(Max)@ I<sub>C</sub> = 4A
- Complement to Type MJ2955

### APPLICATIONS

• Designed for general-purpose switching and amplifier applications

### ABSOLUTE MAXIMUM RATINGS(Ta=25℃)

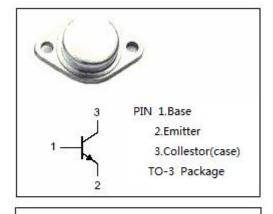
SYMBOL	PARAMETER	VALUE	UNIT			
Vсво	Collector-Base Voltage	100	V			
V <sub>CER</sub>	Collector-Emitter Voltage	70	V			
V <sub>CEO</sub>	Collector-Emitter Voltage	60	V			
V <sub>EBO</sub>	Emitter-Base Voltage	7	V			
lc	Collector Current-Continuous	15	A			
I <sub>B</sub>	Base Current	7	A			
Pc	Collector Power Dissipation@T <sub>C</sub> =25℃	115	W			
T <sub>J,</sub> T <sub>stg</sub>	Operating and Storage Junction Temperature Range	-65~+150	°C			

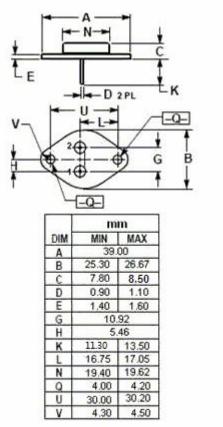
#### THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	МАХ	UNIT
R <sub>th j-c</sub>	Thermal Resistance, Junction to Case	1.52	°C/W

# **Ordering Information**

Product	Package	Packaging
2 N3055T3BL	TO-3	Box





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# **ELECTRICAL CHARACTERISTICS**

 $T_c=25^{\circ}C$  unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	МАХ	UNIT
Vceo(sus)	Collector-Emitter Sustaining Voltage	Ic=30mA ; Iв=0	60		V
V <sub>CE(sat)-1</sub>	Collector-Emitter Saturation Voltage	I <sub>C</sub> = 4A; I <sub>B</sub> = 0.4A		1.1	V
V <sub>CE(sat)-2</sub>	Collector-Emitter Saturation Voltage	I <sub>C</sub> = 10A; I <sub>B</sub> = 3.3A		3.0	V
V <sub>BE(on)</sub>	Base-Emitter On Voltage	I <sub>C</sub> = 4A ; V <sub>CE</sub> = 4V		1.5	V
I <sub>CEO</sub>	Collector Cutoff Current	V <sub>CE</sub> = 30V; I <sub>B</sub> =0		0.7	mA
I <sub>EBO</sub>	Emitter Cutoff Current	V <sub>EB</sub> = 7.0V; I <sub>C</sub> =0		5.0	mA
h <sub>FE-1</sub>	DC Current Gain	I <sub>C</sub> = 4A ; V <sub>CE</sub> = 4V	20	70	
h <sub>FE-2</sub>	DC Current Gain	I <sub>C</sub> = 10A ; V <sub>CE</sub> = 4V	5.0		
I <sub>s/b</sub>	Second Breakdown Collector Current with Base Forward Biased	V <sub>CE</sub> = 40V,t= 1.0s,Nonrepetitive	2.87		А
f⊤	Current Gain-Bandwidth Product	I <sub>C</sub> = 0.5A ; V <sub>CE</sub> = 10V;f=1.0MHz	2.5		MHz

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